VS-P100 Series

RoHS COMPLIANT



Power Modules, Passivated Assembled Circuit Elements, 25 A



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PACE-PAK (D-19)

| PRIMARY CHARACTERISTICS | | | | |
|-------------------------|-------------------------------|--|--|--|
| Ι _Ο | 25 A | | | |
| Туре | Modules - thyristor, standard | | | |
| Package | PACE-PAK (D-19) | | | |

FEATURES

- · Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 V_{RRM}/V_{DRM}
- High dynamic characteristics
- Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-P100 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|-------------------------------------|--------------------------|-------------|------------------|--|--|
| SYMBOL | L CHARACTERISTICS VALUES | | UNITS | | |
| I _O | 85 °C | 25 | А | | |
| 1 | 50 Hz | 357 | А | | |
| ITSM | 60 Hz | 375 | ~ | | |
| l ² t | 50 Hz | 637 | A ² s | | |
| 1-1 | 60 Hz | 580 | A-5 | | |
| l²√t | | 6365 | A²√s | | |
| V _{DRM} , V _{RRM} | | 400 to 1200 | V | | |
| V _{ISOL} | | 2500 | V | | |
| TJ | Range | -40 to +125 | °C | | |
| T _{Stg} | | -40 to +125 | °C | | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | | |
|---------------------------|---|------|---|--|--|
| TYPE NUMBER | NUMBER V _{RRM} /V _{DRM} , MAXIMUM V _{RSM} , MAX REPETITIVE PEAK REVERSE AND NON-REPETIT PEAK OFF-STATE VOLTAGE REVERSE VO V V | | I _{RRM} MAXIMUM AT T _J MAXIMUM mA | | |
| VS-P101, VS-P121, VS-P131 | 400 | 500 | | | |
| VS-P102, VS-P122, VS-P132 | 600 | 700 | | | |
| VS-P103, VS-P123, VS-P133 | 800 | 900 | 10 | | |
| VS-P103, VS-P124, VS-P134 | 1000 | 1100 | | | |
| VS-P105, VS-P125, VS-P135 | 1200 | 1300 | | | |

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| PARAMETER | SYMBOL | | TEST CON | DITIONS | VALUES | UNITS |
|--|--------------------|---|------------------------|--|--------|------------------|
| Maximum DC output current at case | Io | Full bridge | | 25 | А | |
| temperature | IO | i uli biluge | | | 85 | °C |
| | | t = 10 ms | No voltage | | 357 | |
| Maximum peak, one-cycle non-repetitive | I _{TSM} , | t = 8.3 ms | reapplied | | 375 | А |
| on-state or forward current | I _{FSM} | t = 10 ms | 100 % V _{RBM} | | 300 | A |
| | | t = 8.3 ms | reapplied | Sinusoidal half wave, | 315 | |
| Maximum I ² t for fusing | | t = 10 ms | No voltage | ed V _{RRM} | 637 | A ² s |
| | l ² t | t = 8.3 ms | reapplied | | 580 | |
| | 1-1 | t = 10 ms | 100 % V _{BBM} | | 450 | |
| | | t = 8.3 ms | reapplied | | 410 | |
| Maximum I ² \sqrt{t} for fusing | l²√t | t = 0.1 ms to 10 ms, no voltage reapplied $I^{2}t$ for time tx = $I^{2}\sqrt{t} \cdot \sqrt{tx}$ | | 6365 | A²√s | |
| Maximum value of threshold voltage | V _{T(TO)} | T _J = 125 °C | | | 0.82 | V |
| Maximum level value of on-state slope resistance | r _{t1} | T _J = 125 °C, | , average power = | $V_{T(TO)} \ge I_{T(AV)} + r_t + (I_{T(RMS)})^2$ | 12 | mΩ |
| Maximum on-state voltage drop | V _{TM} | $I_{TM} = \pi \times I_{T(A)}$ | AV) | T _J = 25 °C | 1.35 | V |
| Maximum forward voltage drop | V _{FM} | $I_{FM} = \pi \times I_{F(A)}$ | AV) | T _J = 25 °C | 1.35 | V |
| Maximum non-repetitive rate of rise of turned-on current | dl/dt | $\begin{array}{l} T_{J} = 125 \ ^{\circ}\text{C} \ \text{from} \ 0.67 \ \text{V}_{\text{DRM}} \\ I_{\text{TM}} = \pi \ x \ \text{I}_{\text{T(AV)}}, \ \text{I}_{g} = 500 \ \text{mA}, \ t_{r} < 0.5 \ \mu\text{s}, \ t_{p} > 6 \ \mu\text{s} \end{array}$ | | 200 | A/µs | |
| Maximum holding current | Ι _Η | T _J = 25 °C a | anode supply = 6 ' | V, resistive load, gate open | 130 | |
| Maximum latching current | ١L | T _J = 25 °C a | anode supply = 6 | V, resistive load | 250 | mA |

| BLOCKING | | | | |
|--|--|---|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt | T_J = 125 °C, exponential to 0.67 V _{DRM} gate open | 200 | V/µs |
| Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM} | I _{RRM} , I _{DRM} | 1 = 125 C, gate open circuit | | mA |
| Maximum peak reverse leakage current | I _{RRM} | T _J = 25 °C | 100 | μA |
| RMS isolation voltage | V _{ISOL} | 50 Hz, circuit to base, all terminals shorted, T_J = 25 °C, t = 1 s | 2500 | V |

| TRIGGERING | | | | | |
|--|--------------------|--|--------------------|--------|-------|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | VALUES | UNITS |
| Maximum peak gate power | P _{GM} | | | 8 | W |
| Maximum average gate power | P _{G(AV)} | | | 2 | vv |
| Maximum peak gate current | I _{GM} | | | 2 | А |
| Maximum peak negative gate voltage | -V _{GM} | | | 10 | V |
| | | T _J = -40 °C | | 3 | |
| Maximum gate voltage required to trigger | V _{GT} | T _J = 25 °C | | 2 | V |
| | | T _J = 125 °C | Anode supply = | 1 | Í |
| | | $T_J = -40 \ ^{\circ}C$ | 6 V resistive load | 90 | |
| Maximum gate current required to trigger | I _{GT} | T _J = 25 °C | - | 60 | mA |
| | | T _J = 125 °C | | 35 | |
| Maximum gate voltage that will not trigger | V _{GD} | $T_J = 125 \text{ °C}, \text{ rated } V_{DRM} \text{ applied}$ $\frac{0.2}{2}$ | | 0.2 | V |
| Maximum gate current that will not trigger | I _{GD} | | | mA | |

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VS-P100 Series



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| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | |
|---|-----------------------------------|--------------------------------------|-------------|-----------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Maximum junction operating and storage temperature range | T _J , T _{Stg} | | -40 to +125 | °C | |
| Maximum thermal resistance, junction to case per junction | R _{thJC} | DC operation | 2.24 | K/W | |
| Maximum thermal resistance, case to heatsink | R _{thCS} | Mounting surface, smooth and greased | 0.10 | r./ vv | |
| Mounting torque, base to heatsink ⁽¹⁾ | | | 4 | Nm | |
| Approximate weight | | | 58 | g | |
| | | | 2.0 | oz. | |
| Case style | | | PACE-PA | AK (D-19) | |

Note

⁽¹⁾ A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

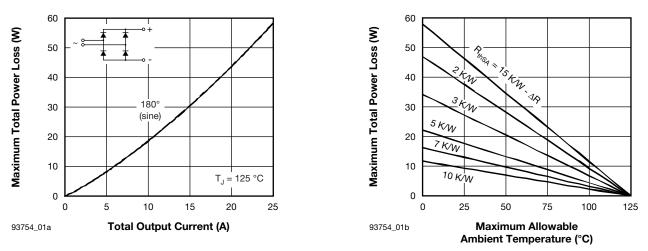


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)

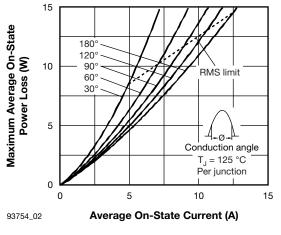


Fig. 2 - On-State Power Loss Characteristics

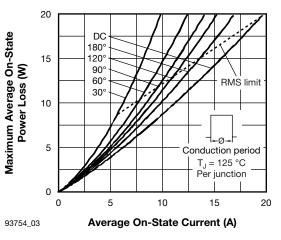


Fig. 3 - On-State Power Loss Characteristics

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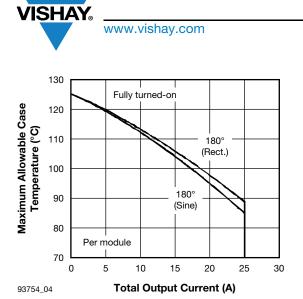


Fig. 4 - Current Ratings Characteristics

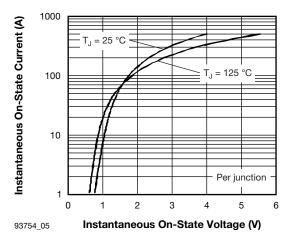
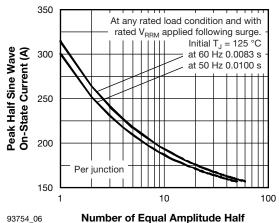


Fig. 5 - On-State Voltage Drop Characteristics



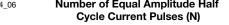
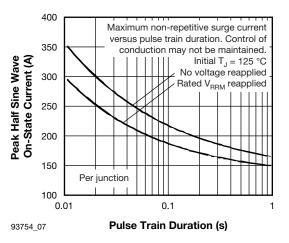
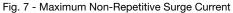
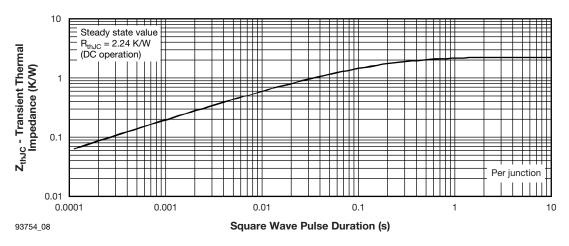


Fig. 6 - Maximum Non-Repetitive Surge Current









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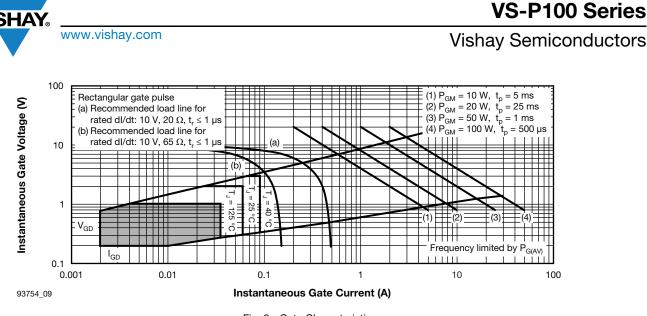


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

| Device code | vs- | Р | 1 | 0 | 2 | к | w | |
|-------------|--------------------------|--|---|--|-------------------------------------|----------|---|--------------------|
| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | I |
| | 1 - 2 - 3 - 4 - | Mo Cur 1 = 4 = Circ 0 = | dule typ rrent rati 25 A D0 40 A D0 cuit cont single p | ng C (P100 C (P400 figuratio bhase, hj | series) series) n ybrid br | idge col | | athode nnection |
| | 5 - | Volt 1 = 2 = 3 = 4 = | tage coo 400 V | bhase, al | II SCR E | 3ridge | | |
| | 6 - 7 - | | - | al voltage al freewl | | | | |



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| CIRCUIT CONFIGUR | CIRCUIT CONFIGURATION | | | | |
|--|----------------------------------|---|--|--|--|
| CIRCUIT DESCRIPTION | CIRCUIT CONFIGURATION CODE | SCHEMATIC DIAGRAM | TERMINAL POSITIONS | | |
| Single phase, hybrid bridge common cathode | 0 | (-) $(-)$ $(+)$ $(+)$ $(+)$ | $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | | |
| Single phase, hybrid bridge doubler connection | 2 | $G1 \circ G2$ AC2 $AC1 \circ$ (-) $C1 \circ C(+)$ | $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | | |
| Single phase, all SCR bridge | 3 | (-) $(-)$ $(+)$ $(+)$ $(+)$ $(+)$ $(+)$ | $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | | |

| CODING ⁽¹⁾ | | | | | |
|--|----------------------------------|-----------------|-----------------------------|-------------------------------|---|
| CIRCUIT DESCRIPTION | CIRCUIT CONFIGURATION CODE | BASIC SERIES | WITH VOLTAGE SUPPRESSION | WITH FREEWHEELING DIODE | WITH BOTH VOLTAGE SUPPRESSION AND FREEWHEELING DIODE |
| Single phase, hybrid bridge common cathode | 0 | P10. | P10.K | P10.W | P10.KW |
| Single phase, hybrid bridge doubler connection | 2 | P12. | P12.K | - | - |
| Single phase, all SCR bridge | 3 | P13. | P13.K | - | - |

Note

⁽¹⁾ To complete code refer to Voltage Ratings table, i.e.: for 600 V P10.W complete code is P102W

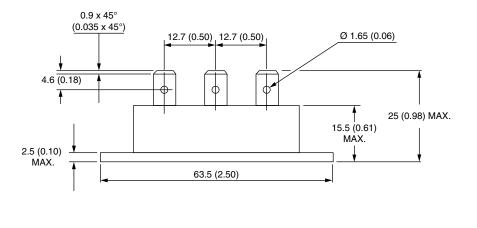
| LINKS TO RELATED DOCUMENTS | | | |
|----------------------------|--------------------------|--|--|
| Dimensions | www.vishay.com/doc?95335 | | |

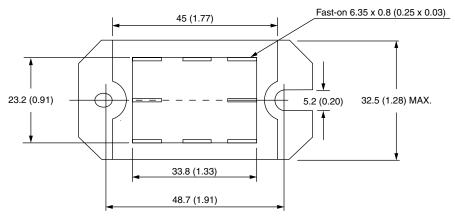
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D-19 PACE-PAK

DIMENSIONS in millimeters (inches)

SHA







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